

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of: **INOUE, et al.**

Group Art Unit: 2814

Serial No.: 09/473,988

Examiner: DOAN, Theresa T.

Filed: December 29, 1999

P.T.O. Confirmation No.: 1714-*Ex-19*

For: **SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME**

Frater  
Jim  
(M)

## **PRELIMINARY AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Date: July 8, 2003

Sir:

Prior to continued examination, please amend the above-captioned patent application as follows:

**IN THE CLAIMS:**

**Please amend claims 1 and 8 as follows:**

1. (Five Times Amended) A semiconductor device comprising an insulating interlayer formed on a conductive film, said insulating interlayer including:

- a first insulating layer of a composition containing SiH;
- a second insulating layer formed on said first insulating layer; and
- a third insulating layer formed between said conductive film and said first insulating layer, wherein said first insulating layer has an H content of not less than 15.4 atom% in the